

L Number	Hits	Search Text	DB	Time stamp
1	5150	(1177/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:00
8	3	("51101").PN.	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:37
15	2	("51101" "5216000").PN.	USPAT	2002/08/29 07:47
16	0	("51101" "51467").PN.) and organic with EL electroluminescence electroluminescent	USPAT	2002/08/29 07:46
17	0	("51101" "51467").PN.) and organic with EL electroluminescence electroluminescent	USPAT	2002/08/29 07:46
18	3	semiconductor-energy-laboratory.as.	USPAT	2002/08/29 07:48
19	4	semiconductor-energy-laboratory.as.	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:51
26	7	semicon. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor.	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 07:55
33	3	semicon. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor and (organic with (EL electroluminescent electroluminescent)	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:00
40	0	semicon. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor and (organic with (EL electroluminescent electroluminescent)	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:00
47	2	(1177/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:38
54	2	(1177/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:43
61	8	(1177/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:44
68	8	(1177/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and gas	USPAT; US-PGPHUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 08:44

140	6	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2)	USPAT; US-PSPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:21
147	3	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:24
153	3	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:12
159	3	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:26
165	3	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:27
171	1	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28
177	1	((257/53) or (257/59) or (257/66) or (257/67) or (257/72) or (257/73) or (257/74) or (313/512) or (448/15).CCLS.) and active adj matrix and (organic with (EL electroluminescence) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal) and (helium ne argon or krypton or xenon or nitrogen n2) and (helium ne argon or krypton or xenon or nitrogen n2) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:28

183

1 ((1257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)

USPAT;
EPO; JPO;
DERWENT;
IBM_TDB

2002/08/29 10:29

189

1 ((1257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitrogen ni) and (helium he argon ar krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)

USPAT;
EPO; JPO;
DERWENT;
IBM_TDB

2002/08/29 11:14

195

4 ((1257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal

USPAT;
EPO; JPO;
DERWENT;
IBM_TDB

2002/08/29 11:20

201

1 ((1257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal

USPAT;
EPO; JPO;
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2002/08/29 11:15

207

4 ((1257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and matrix and (organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal

USPAT;
EPO; JPO;
DERWENT;
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2002/08/29 11:21

229 445/25).CCLS.

USPAT 2002/08/28 14:30

343 313/512).CCLS.

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0 257/347).ap.

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US-PGPUB;

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US-PGPUB;

EPO; JPO;

DERWENT;

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USPAT

2002/08/28 14:48

USPAT;

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EPO; JPO;

DERWENT;

IBM_TDB

17	((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 14:55
13	((313/512) or (445/25)).CCLS.) and active adj matrix) and crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 14:56
1	((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 14:58
3	5672.83.URFN.	USPAT;	2002/08/28 14:57
1	((313/512) or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:01
0	(257/5).ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:01
134751	(257/5).ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:02
66945	(313/5).ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:02
8	((257/5).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:04
5	((257/5).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:32
0	((313/5).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:25
4347	((257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 16:14
2	((257/57) or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 08:36
4396	yamazaki-shunpei.in. or arai-yasuyuki.in.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/28 15:31

4178 yamazaki-shunpei.in.

USPAT; 2002/08/28 15:31

US-PGPUB;

EPO; JPO;

DEFWENT;

IBM_TDE

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USPAT;

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US-PGPUB

USPAT;

2002/08/28 15:33

US-PGPUB;

EPO; JPO;

DEFWENT;

IBM_TDB

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USPAT;

US-PGPUB;

EPO; JPO;

DEFWENT;

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USPAT;

2002/08/28 16:15

US-PGPUB;

EPO; JPO;

DEFWENT;

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USPAT;

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EPO; JPO;

DEFWENT;

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2002/08/28 16:15

USPAT;

US-PGPUB;

EPO; JPO;

DEFWENT;

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2002/08/28 16:27

943 yamazaki-shunpei.in. or arai-yasuyuki.in.

1171 yamazaki-shunpei.in. or arai-yasuyuki.in.

0 (yamazaki-shunpei.in. or
arai-yasuyuki.in.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET) and single
adj crystal

1 (yamazaki-shunpei.in. or
arai-yasuyuki.in.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET) and single
adj crystal

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(257/66) or (257/72) or (257/347) or
(257/350)).CCLS.) and active adj matrix
and (organic with EL) and gate with (field
adj effect adj transistor FET mostft) and
single adj crystal

5136 ((257/57) or (257/59) or (257/66) or
(257/66) or (257/72) or (257/347) or
(257/350) or (313/512) or (445/25)).CCLS.

2 ((257/57) or (257/59) or (257/66) or
(257/66) or (257/72) or (257/347) or
(257/350) or (313/512) or (445/25)).CCLS.)
and active adj matrix and (organic with
EL) and gate with (field adj effect adj
transistor FET mostft) and single adj
crystal

2 ("6153893" | "6246070").PN.